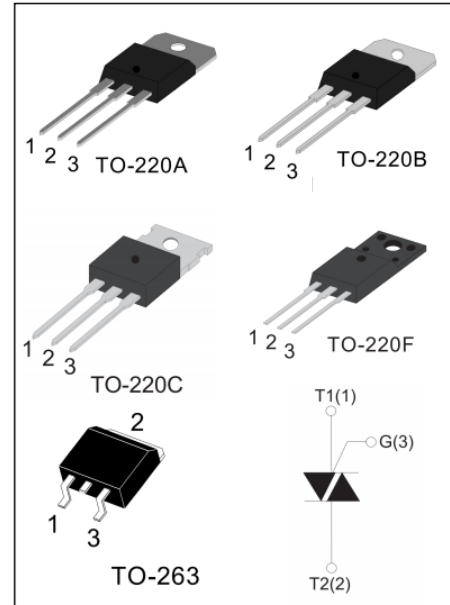


T2025/F2025 Series 20A TRIAC

Rev: 1.0

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM}/V_{RRM}	800	V
I_{GT3}	25	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 ~150	°C
Operating junction temperature range	T_j	-40~125	°C
Repetitive peak off-state voltage ($T=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T=25^{\circ}C$)	V_{RRM}	800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} +100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} +100$	V
TO-220A $T_c = 70^{\circ}C$ TO-220B $T_c = 80^{\circ}C$ TO-220C $T_c = 75^{\circ}C$ TO-220F $T_c = 75^{\circ}C$ TO-263 $T_c = 100^{\circ}C$	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle, $F=50Hz$)	I_{TSM}	200	A
I^2t value for fusing ($t_p=10ms$)	I^2t	156	A^2S
Critical rate of rise of on-state current ($I=2 \times I_{GT}$)	dI/dt	50	$A/\mu S$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)
3 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V = 12V$ $R = 33\Omega$	I II III	MAX.	25	mA
V_{GT}		I II III	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ C$ $R = 3.3K\Omega$	I II III	MIN.	0.2	V
I_L	$I_G = 1.2I_{GT}$	I II III	MAX.	60	mA
I_H	$I_T = 100mA$		MAX.	40	mA
dV/dt	$V_D = 2/3 V_{DRM}$ Gate Open $T_j = 125^\circ C$		MIN.	400	V/ μs
(dV/dt)c	Without snubber $T_j = 125^\circ C$		MIN.	10	V/ μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V = 12V$ $R = 33\Omega$	I II III	MAX.	25	mA
		IV		50	
V_{GT}		I II III IV	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ C$ $R = 3.3K\Omega$	I II III IV	MIN.	0.2	V
I_L	$I_G = 1.2I_{GT}$	I III IV	MAX.	60	mA
		II		100	
I_H	$I_T = 100mA$		MAX.	40	mA
dV/dt	$V_D = 2/3 V_{DRM}$ Gate Open $T_j = 125^\circ C$		MIN.	20	V/ μs
(dV/dt)c	(dI/dt)c = 5.3 A/ms $T_j = 125^\circ C$		MIN.	5	V/ μs

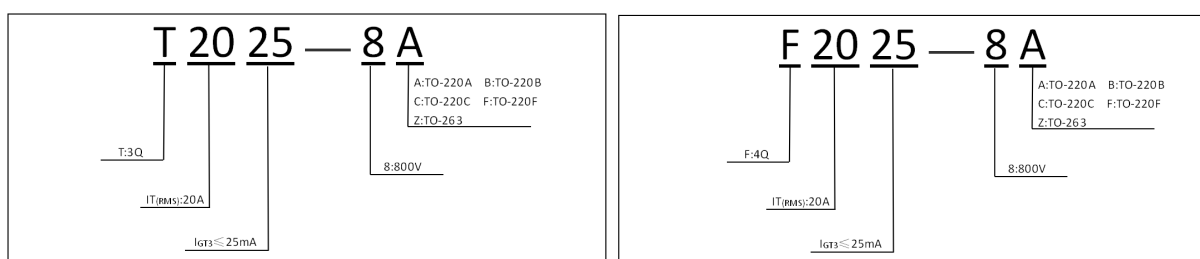
STATIC CHARACTERISTICS

Symbol	Parameter		Value	Unit
V_{TM}	$I_{TM} = 28A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	1.55	V
I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	10	μA
I_{RRM}		$T_j = 125^\circ C$	3	mA

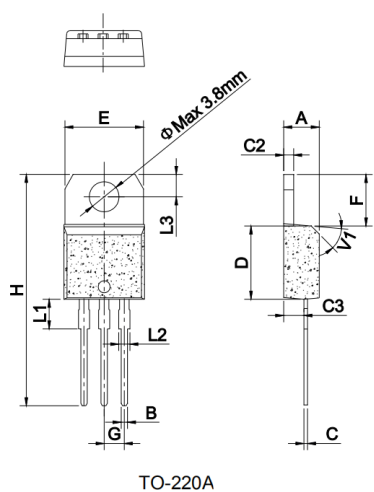
Thermal Resistances

Symbol	Parameter	Value	Unit
Rth(j-a)	junction to ambient	TO-263	45
		TO-220F	50
		TO-263	60
Rth(j-c)	Junction to case(AC)	TO-263	1.1
		TO-220M2	1.9
		TO-220F	2.7

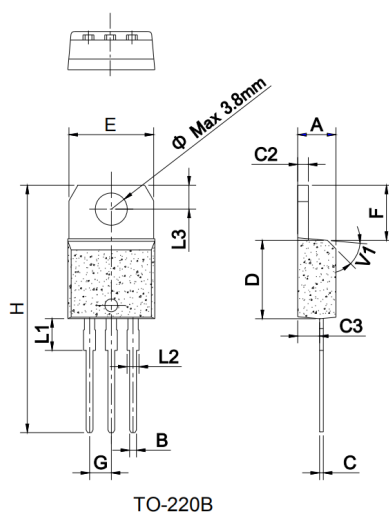
Ordering Information Scheme



Package Mechanical Data

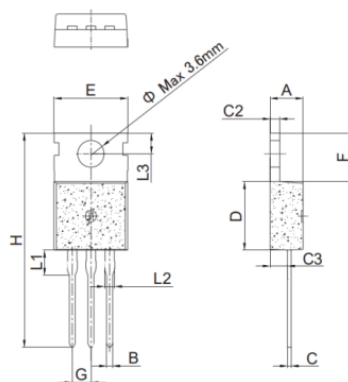


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



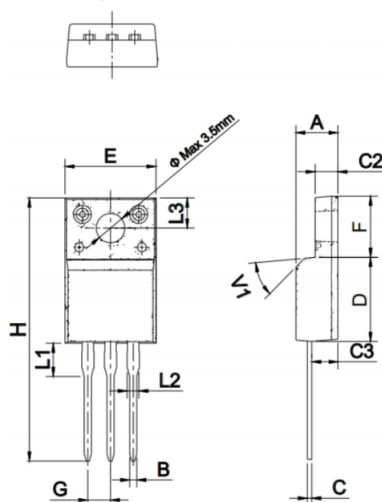
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Package Mechanical Data



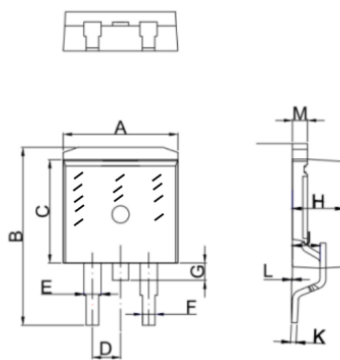
TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.30		1.48	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	



TO-220F

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.50		3.10	0.096		0.108
C3	2.40		2.80	0.102		0.118
D	8.60		8.90	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.70		7.50	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.5	0.390		0.402
B	14.70		15.80	0.579		0.622
C	8.8		9.2	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0		0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FIG.1:Maximum power dissipation versus RMS on-state current(full cycle)

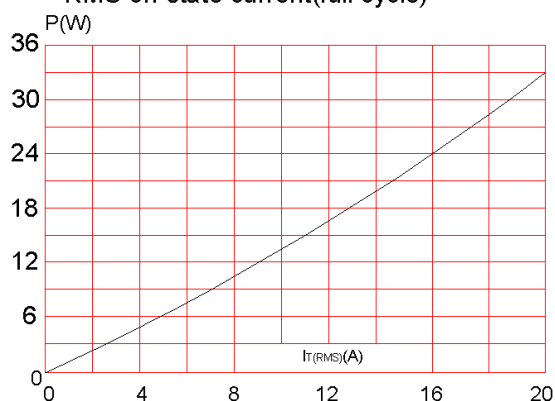


FIG.2:RMS on-state current versus mounting base temperature(full cycle)

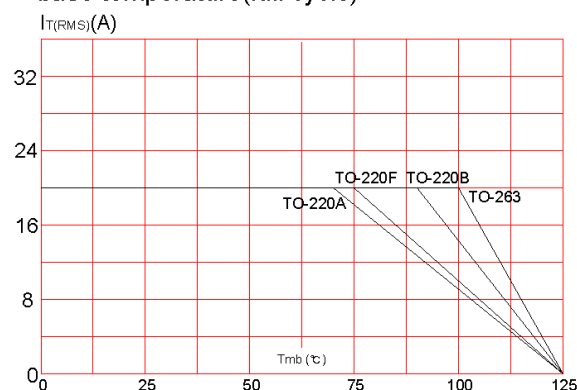


FIG.3:On-state characteristics (maximum values).

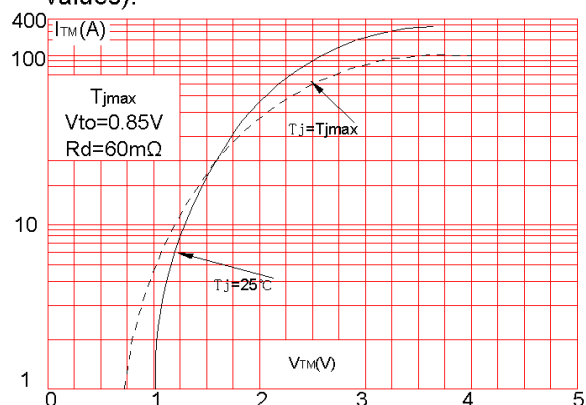


FIG.4:Surge peak on-state current versus number of cycles.

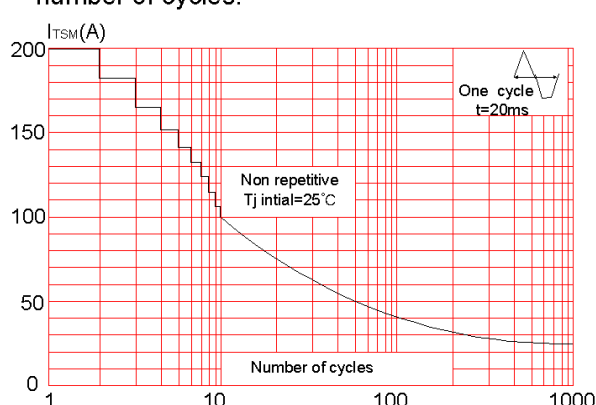


FIG.5:Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms,and corresponding value of I²t.

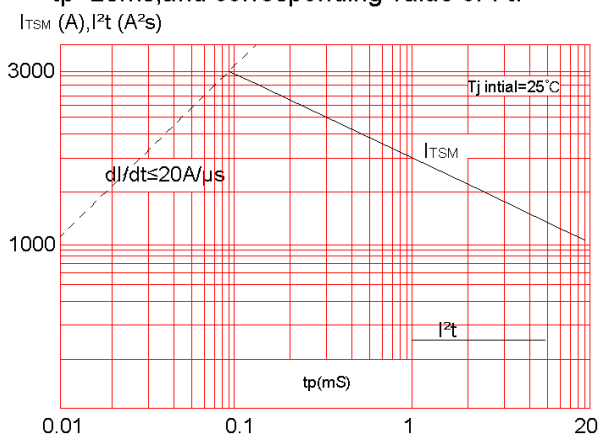


FIG.6:Relative variations of gate trigger current,holding current and latching current versus junction temperature(typical values)

